



### **60V N-Channel Enhancement Mode MOSFET**

Voltage

60 V

Current

33 A

#### **Features**

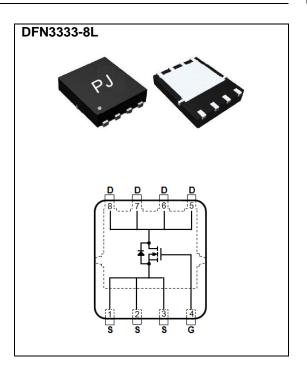
- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@15A<21m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_{D}@8A<24m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER   |                       | SYMBOL          | LIMIT       | UNITS |  |
|---|-----------------------|-----------------|-------------|-------|--|
| Drain-Source Voltage                              |                       | $V_{DS}$        | 60          | .,,   |  |
| Gate-Source Voltage                               |                       | $V_{GS}$        | <u>+</u> 20 | V     |  |
| Continuous Drain Current                          | T <sub>C</sub> =25°C  | I <sub>D</sub>  | 33          | A     |  |
|   | T <sub>C</sub> =100°C |                 | 21          |       |  |
| Pulsed Drain Current <sup>(Note 1)</sup>          | T <sub>C</sub> =25°C  | I <sub>DM</sub> | 132         |       |  |
| Power Dissipation                                 | T <sub>C</sub> =25°C  | Po              | 44.6        | W     |  |
|   | T <sub>C</sub> =100°C |                 | 18          |       |  |
| Continuous Drain Current                          | T <sub>A</sub> =25°C  | I <sub>D</sub>  | 6           | А     |  |
|   | T <sub>A</sub> =70°C  |                 | 5           |       |  |
| Power Dissipation                                 | T <sub>A</sub> =25°C  | -               | 2.0         | W     |  |
| Power Dissipation                                 | T <sub>A</sub> =70°C  | Pb              | 1.3         |       |  |
| Single Pulse Avalanche Energy <sup>(Note 6)</sup> |                       | E <sub>AS</sub> | 42          | mJ    |  |
| Operating Junction and Storage Temperature Range  |                       | $T_J, T_{STG}$  | -55~150     | °C    |  |
| Typical Thermal Resistance (Note 4,5)             | Junction to Case      | $R_{	heta JC}$  | 2.8         | °C/W  |  |
|   | Junction to Ambient   | $R_{\theta JA}$ | 62.5        |       |  |

• Limited only By Maximum Junction Temperature





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION   | MIN. | TYP. | MAX.         | UNITS |
|----------------------------------|---------------------|--|------|------|--------------|-------|
| Static                           |                     |  |      |      |              |       |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA<br>V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA | 60   | -    | -            | V     |
| Gate Threshold Voltage           | $V_{GS(th)}$        |  | 1.0  | 1.73 | 2.5          |       |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =15A  | -    | 18   | 21           | mΩ    |
|                                  |                     | V <sub>GS</sub> =4.5V, I <sub>D</sub> =8A  | -    | 21   | 24           |       |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V  | -    | -    | 1.0          | uA    |
| Gate-Source Leakage Current      | I <sub>GSS</sub>    | V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V  | -    | -    | <u>+</u> 100 | nA    |
| Dynamic (Note 5)                 |                     |  |      |      |              |       |
| Total Gate Charge                | $Q_g$               | V <sub>DS</sub> =30V, I <sub>D</sub> =15A,<br>V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>               | -    | 28   | -            | nC    |
| Gate-Source Charge               | $Q_gs$              |  | -    | 3.5  | -            |       |
| Gate-Drain Charge                | $Q_{gd}$            |  | -    | 6.5  | -            |       |
| Input Capacitance                | Ciss                | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,<br>f=1.0MHZ   | -    | 1680 | -            | pF    |
| Output Capacitance               | Coss                |  | -    | 115  | -            |       |
| Reverse Transfer Capacitance     | Crss                | I=1.0WITZ  | -    | 85   | -            |       |
| Turn-On Delay Time               | td <sub>(on)</sub>  |  | -    | 7.2  | -            | ns    |
| Turn-On Rise Time                | t <sub>r</sub>      | $V_{DD}$ =30V, $I_{D}$ =1A,<br>$V_{GS}$ =10V, $R_{G}$ =6 $\Omega$<br>(Note 1,2)                        | -    | 38   | -            |       |
| Turn-Off Delay Time              | td <sub>(off)</sub> |  | -    | 34   | -            |       |
| Turn-Off Fall Time               | t <sub>f</sub>      |  | -    | 8.2  | -            |       |
| Drain-Source Diode               |                     |  |      |      |              |       |
| Maximum Continuous Drain-Source  | ,                   |  | -    | -    | 33           | А     |
| Diode Forward Current            | I <sub>S</sub>      |  |      |      |              |       |
| Reverse Recovery Time            | $V_{SD}$            | I <sub>S</sub> =1A, V <sub>GS</sub> =0V  | -    | 0.68 | 1            | V     |

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. The test condition is L=0.1mH,  $I_{AS}$ =29A,  $V_{DD}$ =25V,  $V_{GS}$ =10V, Starting  $T_J$ =25°C
- 7. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

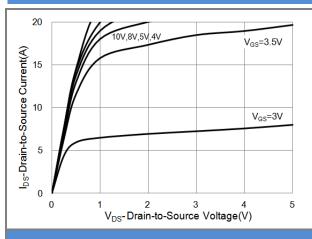
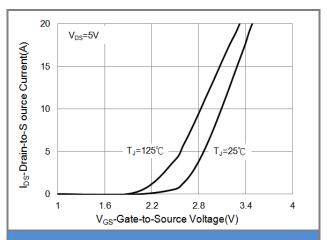


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

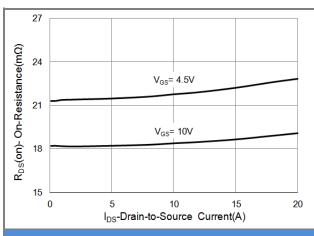


Fig.3 On-Resistance vs. Drain Current

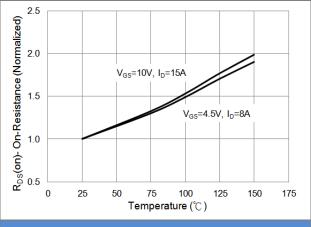
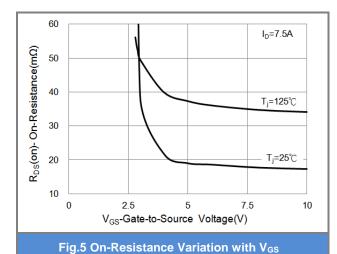


Fig.4 On-Resistance vs. Junction temperature



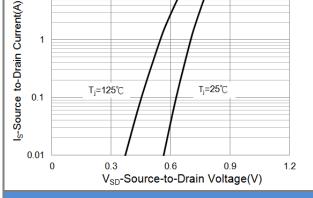


Fig.6 Source-Drain Diode Forward Voltage

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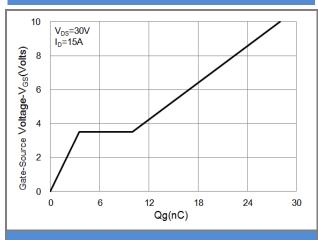


Fig.7 Gate-Charge Characteristics

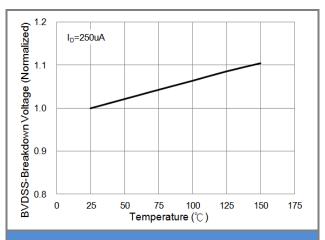


Fig.8 Breakdown Voltage Variation vs. Temperature

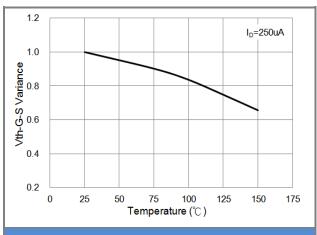


Fig.9 Threshold Voltage Variation with Temperature

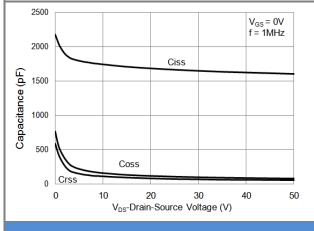
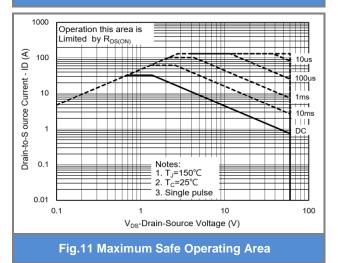


Fig.10 Capacitance vs. Drain-Source Voltage







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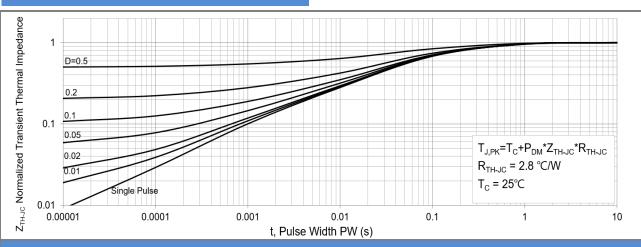


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

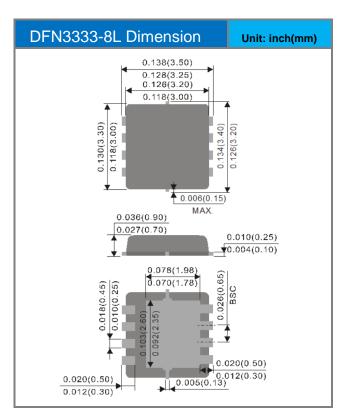


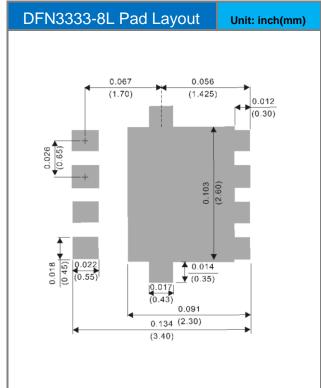


### **Part No Packing Code Version**

| Part No Packing Code | Package Type | Packing Type      | Marking | Version      |
|----------------------|--------------|-------------------|---------|--------------|
| PJQ4466AP_R2_00001   | DFN3333-8L   | 5K pcs / 13" reel | 4466    | Halogen free |

### **Packaging Information & Mounting Pad Layout**









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